Vishay Semiconductors

SOT-227 Silicon Carbide Single Phase Bridge, 90 A



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LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _O at T _C = 115 °C	90 A				
V _{RRM}	1200 V				
V_{FM} at 90 A, T_C = 25 °C	1.9 V				
Туре	Modules - diode, SiC Schottky				
Package	SOT-227				
Circuit configuration	Single phase bridge				

FEATURES

- Virtually no recovery tail and no switching losses
- Pb-free RoHS

COMPLIANT

- Majority carrier diode using Schottky technology on SiC wide band gap material
- Improved V_F and efficiency by thin wafer technology
- · High speed switching, low switching losses
- · Positive temperature coefficient, for easy paralleling
- Electrically isolated base plate
- Large creepage distance between terminal
- · Simplified mechanical designs, rapid assembly
- Designed and qualified for industrial level
- UL approved file E78996
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 1200 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS	CHARACTERISTICS VALUES					
1	180° rect. conduction angle	90	А				
IO	T _C	115	°C				
1	50 Hz	500	А				
IFSM	60 Hz	524	A				
l ² t	50 Hz	538	A ² s				
1-1	60 Hz	491	A-5				
V _{RRM}		1200	V				
TJ		-40 to +175	°C				

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS		
TYPE NUMBER	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V
VS-SC90BA120	1200	1200

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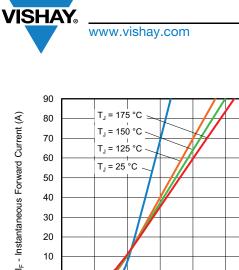
ELECTRICAL SPECIFICATIONS PER DIODE (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS MIN. TYP.		TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	I _R = 300 μA	1200	-	-		
Forward voltage		I _F = 90 A		1.66	1.90	V	
Forward voltage	V _{FM}	I _F = 90 A, T _J = 150 °C	-	2.48	-		
		V _R = 1200 V	-	1.9	180		
Reverse leakage current	I _{RM}	$T_J = 125 \ ^{\circ}C, V_R = 1200 \ V$	-	6.8	-	μA	
		$T_{\rm J} = 150 \ ^{\circ}{\rm C}, V_{\rm R} = 1200 \ {\rm V}$	-	10.0	-		
Junction capacitance	CT	V _R = 1200 V, f = 1 MHz	-	206	-	pF	

FORWARD CONDUCTION								
PARAMETER	SYMBOL		TEST CONDITIO	NS	VALUES	UNITS		
Maximum DC output current	l.	Resistive or inc	ductive load		90	А		
at case temperature	lo				115	°C		
		t = 10 ms	No voltage		500			
Maximum peak, one-cycle		t = 8.3 ms	reapplied		524	A		
non-repetitive forward current	IFSM	t = 10 ms	100 % V _{RRM}		421			
		t = 8.3 ms	reapplied		440			
		t = 10 ms	No voltage	Initial T _J = 25 °C	1253			
Maximum I ² t for fusing	12+	12+	l ² t	t = 8.3 ms	reapplied		1144	A ² s
Maximum r-t for fusing	1-1	t = 10 ms 100 % V _{BBM}		886	A-S			
		t = 8.3 ms	reapplied		809			
Maximum I ² \sqrt{t} for fusing	l²√t	$I^{2}t$ for time $t_{x} = I_{2}\sqrt{t} x \sqrt{t_{x}}$; 0.1 $\leq t_{x} \leq$ 10 ms, $V_{RRM} = 0 V$			12.53	kA²√s		
Low level of threshold voltage, per leg	V _{F(T0)1}	(16.7.0(x-x)) + (x-x) = T = T			0.81	V		
Low level value of forward slope resistance	r _{f1}	$(16.7 \% x \pi x I_{F(AV)}) < I < \pi x I_{F(AV)}, T_J = T_J \text{ maximum}$ $22.71 \text{ m}\Omega$				mΩ		
High level of threshold voltage, per leg	V _{F(T0)2}				0.88	V		
High level value of forward slope resistance	r _{f2}	$(I > \pi \times I_{F(AV)}), T_J = T_J \text{ maximum}$ $22.62 \text{ m}\Omega$				mΩ		

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL TEST CONDITIONS MIN. TYP. MAX. UNITS						
Total capacitive charge	Q _C	V _R = 800 V	-	332	-	nC	

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Junction-to-case, per diode	R _{thJC}		-	-	0.46	°C/W	
Case-to-heatsink	R _{thCS}	Flat, greased surface	-	0.1	-	0/00	
Weight			-	30	-	g	
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)	
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)	
Case style			SOT-227				

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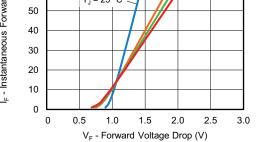


Fig. 1 - Typical Forward Voltage Drop Characteristics

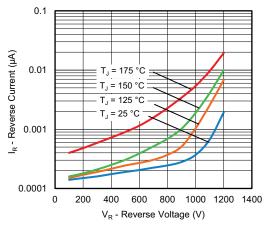


Fig. 2 - Typical Values of Reverse Current vs Reverse Voltage

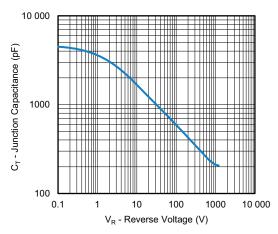


Fig. 3 - Junction Capacitance vs. Reverse Voltage

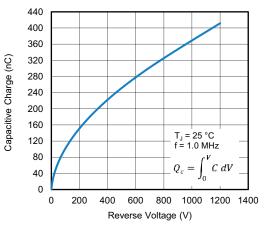


Fig. 4 - Typical Capacitive Charge vs. Reverse Voltage

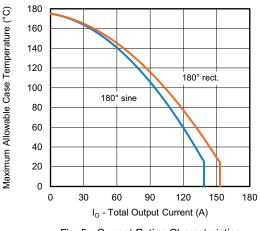


Fig. 5 - Current Rating Characteristics

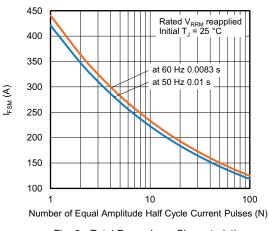


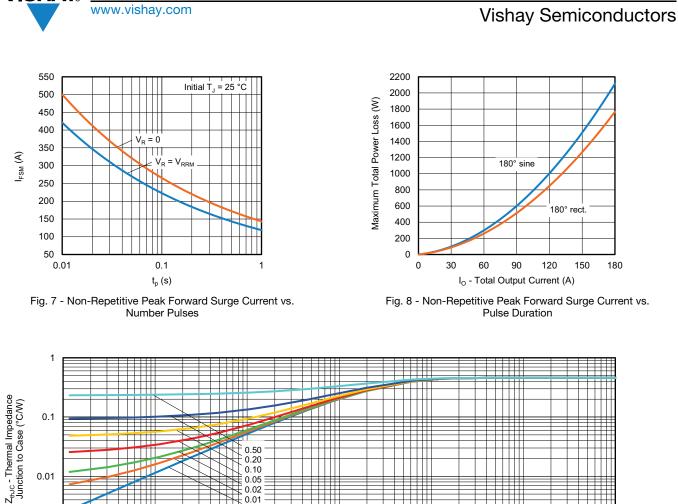
Fig. 6 - Total Power Loss Characteristics

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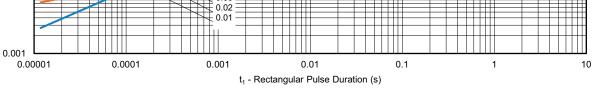


Fig. 9 - Maximum Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

SHA

							I
Device code	VS-	S	С	90	В	Α	120
	1	2	3	4	5	6	7
	1 -	Visl	nay Sem	niconduc	ctors pro	oduct	
	2 -	- Silicon Carbide diode					
	3 -	- Present silicon generation					
	4 -	- Current rating (90 = 90 A)					
	5 -	Circ	uit conf	iguratior	n (single	e phase	bridge)
	6 -	Pac	kage in	dicator (SOT-22	27 stand	lard ins
	7 -	Volt	age rati	ng (120	= 1200	V)	

Quantity per tube is 10, M4 screw and washer included

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VS-SC90BA120



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CIRCUIT CONFIGURATION							
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING					
Single phase bridge	В	(AC) 4 0 0 3 (-) 4 0 0 3 (-) 4 0 0 3 (-) 4 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0					

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95423
Part marking information	www.vishay.com/doc?95425



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